

2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)



ON Semiconductor®

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Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- High DC Current Gain
- High Current Gain – Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

| Rating | Symbol | Value | Unit |
|------------------------------------------------------------------------------------------|----------------|----------------|--------------------------|
| Collector-Emitter Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292 | V_{CEO} | 30 50 70 | Vdc |
| Collector-Base Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292 | V_{CB} | 40 60 80 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | Vdc |
| Collector Current – Continuous | I_C | 7.0 | Adc |
| Collector Current – Peak | I_{CM} | 10 | Adc |
| Base Current | I_B | 3.0 | Adc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 40 0.32 | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |

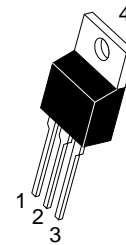
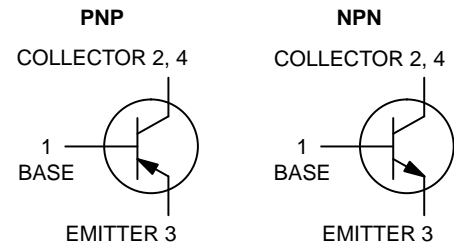
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Max | Unit |
|--------------------------------------|-----------------|-------|--------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 3.125 | $^\circ\text{C/W}$ |

7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30 – 50 – 70 VOLTS, 40 WATTS



TO-220
CASE 221A
STYLE 1

MARKING DIAGRAM



2N6xxx = Specific Device Code
xxx = See Table on Page 4
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

| Characteristic | Symbol | Min | Max | Unit |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|----------------------------|----------------------------------------|-------------------------------------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 100\text{ mAdc}$, $I_B = 0$) 2N6111, 2N6288 2N6109 2N6107, 2N6292 | $V_{CE(sus)}$ | 30 50 70 | – – – | Vdc |
| Collector Cutoff Current ($V_{CE} = 20\text{ Vdc}$, $I_B = 0$) 2N6111, 2N6288 ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) 2N6109 ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$) 2N6107, 2N6292 | I_{CEO} | – – – | 1.0 1.0 1.0 | mAdc |
| Collector Cutoff Current ($V_{CE} = 40\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) 2N6111, 2N6288 ($V_{CE} = 60\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) 2N6109 ($V_{CE} = 80\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$) 2N6107, 2N6292 ($V_{CE} = 30\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) 2N6111, 2N6288 ($V_{CE} = 50\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) 2N6109 ($V_{CE} = 70\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$, $T_C = 150^\circ\text{C}$) 2N6107, 2N6292 | I_{CEX} | – – – – – – | 100 100 100 2.0 2.0 2.0 | μAdc mAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | – | 1.0 | mAdc |

ON CHARACTERISTICS (Note 3)

| | | | | |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-----------------------|------------------------|-----|
| DC Current Gain ($I_C = 2.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) 2N6107, 2N6292 ($I_C = 2.5\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) 2N6109 ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) 2N6111, 2N6288 ($I_C = 7.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) All Devices | h_{FE} | 30 30 30 2.3 | 150 150 150 – | – |
| Collector–Emitter Saturation Voltage ($I_C = 7.0\text{ Adc}$, $I_B = 3.0\text{ Adc}$) | $V_{CE(sat)}$ | – | 3.5 | Vdc |
| Base–Emitter On Voltage ($I_C = 7.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) | $V_{BE(on)}$ | – | 3.0 | Vdc |

DYNAMIC CHARACTERISTICS

| | | | | |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|-----------|--------|-----|
| Current Gain – Bandwidth Product (Note 4) ($I_C = 500\text{ mAdc}$, $V_{CE} = 4.0\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$) 2N6288, 2N6292 2N6107, 2N6109, 2N6111 | f_T | 4.0 10 | – – | MHz |
| Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) | C_{ob} | – | 250 | pF |
| Small–Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 50\text{ kHz}$) | h_{fe} | 20 | – | – |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$

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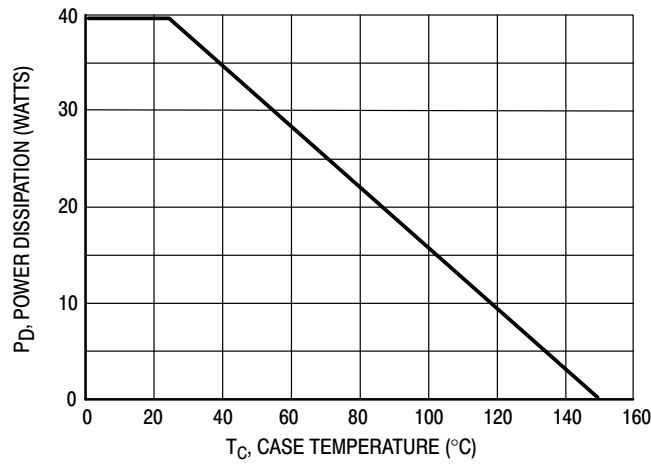


Figure 1. Power Derating

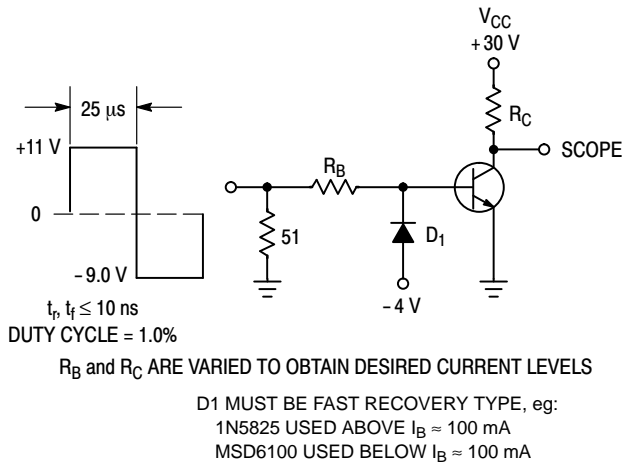


Figure 2. Switching Time Test Circuit

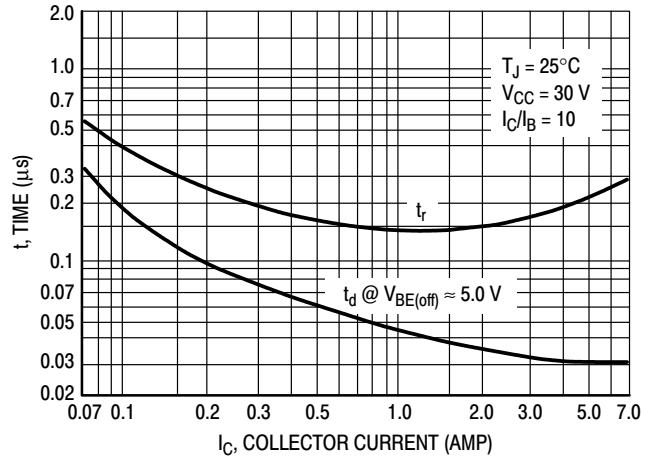


Figure 3. Turn-On Time

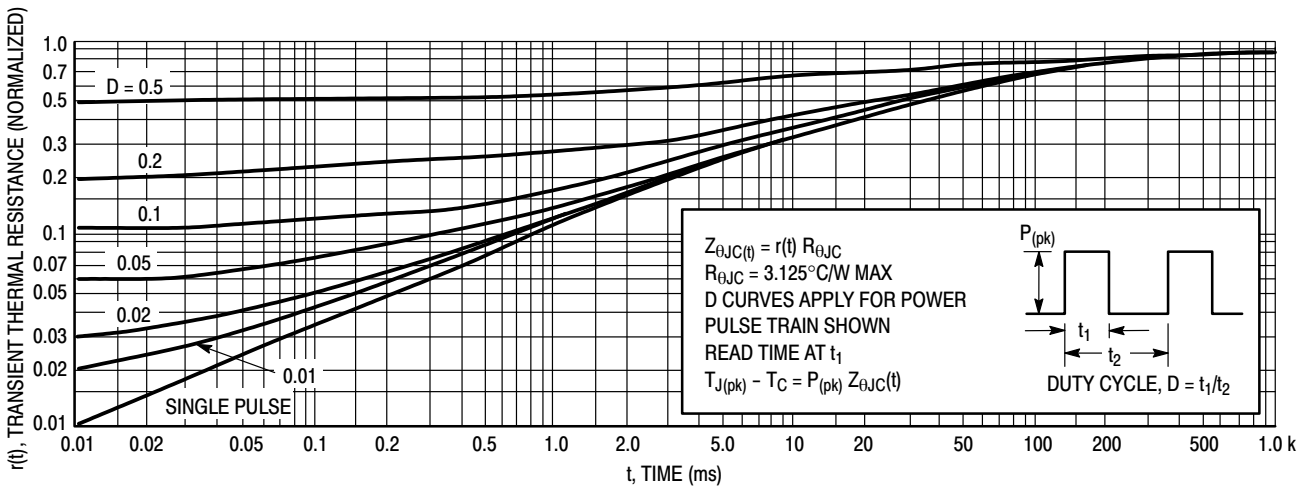


Figure 4. Thermal Response

2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

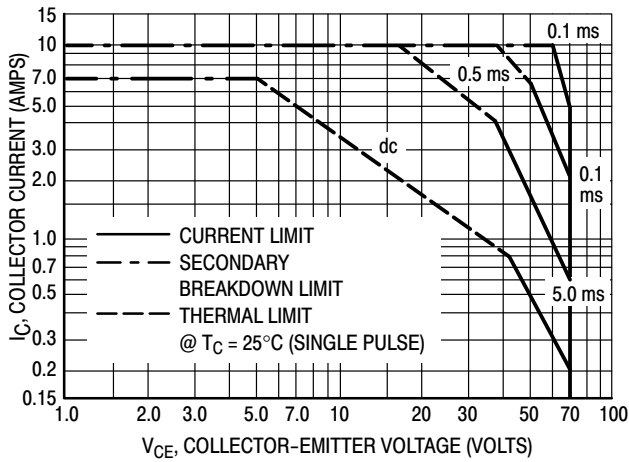


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

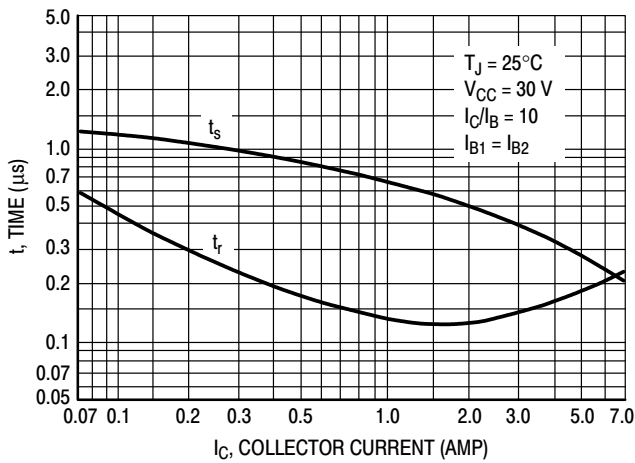


Figure 6. Turn-Off Time

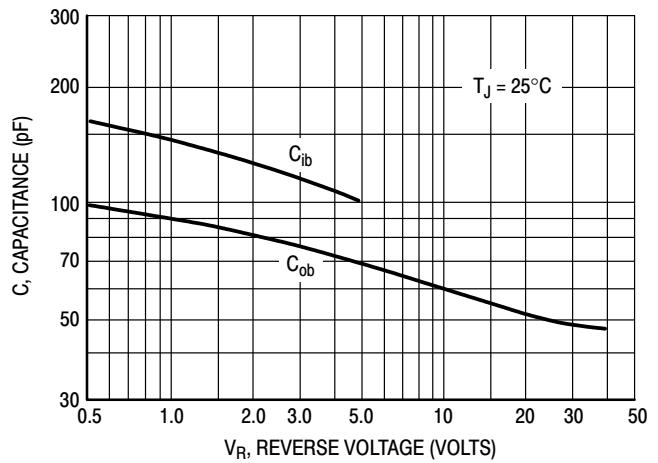


Figure 7. Capacitance

ORDERING INFORMATION

| Device | Device Marking | Package | Shipping |
|---------|----------------|---------------------|-----------------|
| 2N6107G | 2N6107 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6109G | 2N6109 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6111G | 2N6111 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6288G | 2N6288 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6292G | 2N6292 | TO-220 (Pb-Free) | 50 Units / Rail |

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